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2SB0774 (2SB774)

Silicon PNP epitaxial planar type

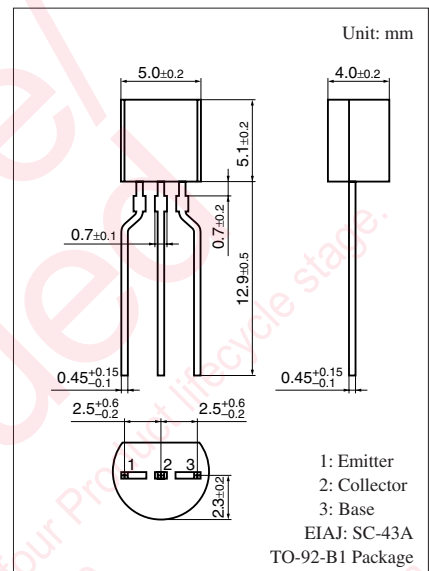
For low-frequency amplification

■ Features

- High emitter-base voltage (Collector open) V_{EBO}
- Protective diodes and resistances between emitter and base can be omitted.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-25	V
Emitter-base voltage (Collector open)	V_{EBO}	-15	V
Collector current	I_C	-100	mA
Peak collector current	I_{CP}	-200	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

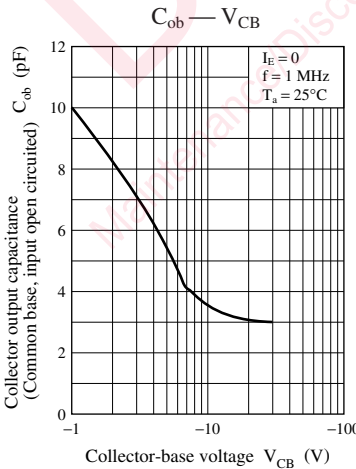
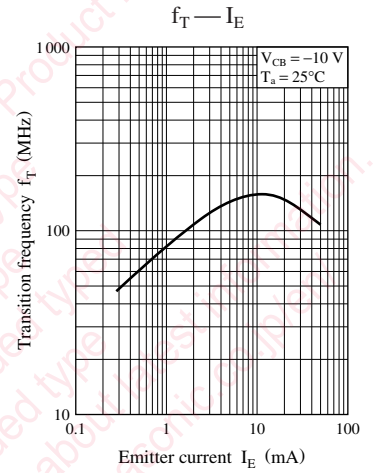
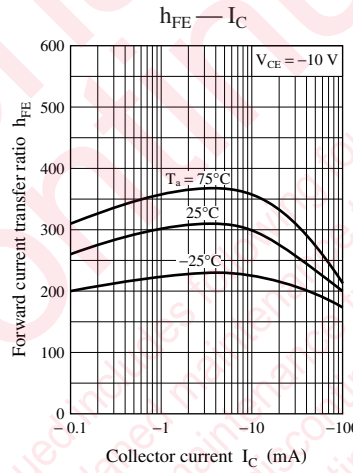
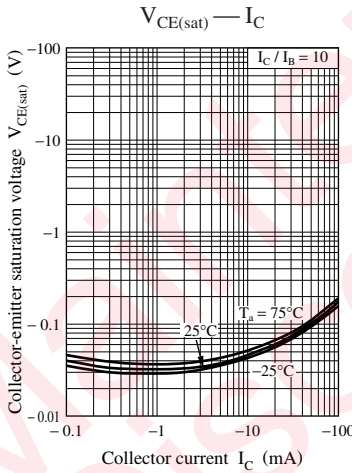
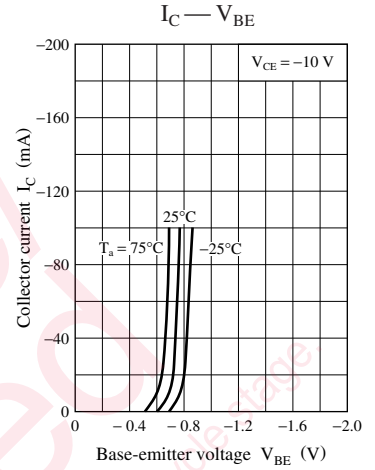
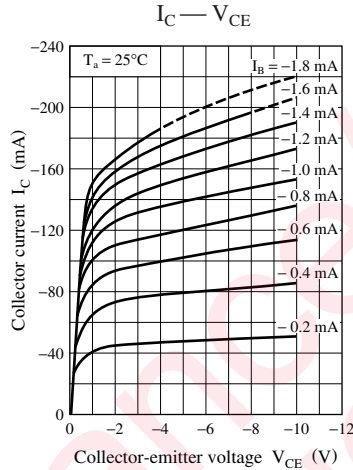
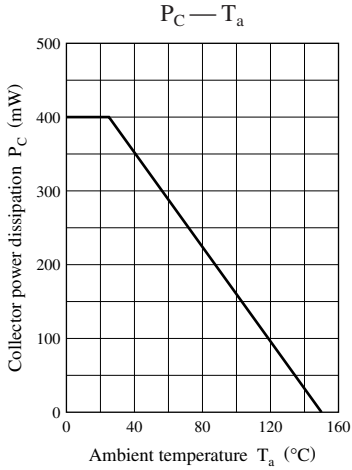
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-25			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -20 \text{ V}, I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	210		460	—
	h_{FE2}	$V_{CE} = -2 \text{ V}, I_C = -100 \text{ mA}$	90			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance (Common-emitter reverse transfer)	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S
h_{FE1}	210 to 340	290 to 460

Note) The part number in the parenthesis shows conventional part number.



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